

# **BUK9Y3R0-40E**

### N-channel 40 V 3.0 m $\Omega$ logic level MOSFET in LFPAK56 11 November 2014

**Product data sheet** 

#### **General description** 1.

Logic level N-channel MOSFET in LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### **Features and benefits** 2.

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V<sub>GS(th)</sub> rating of greater than 0.5 V at 175 °C

## **Applications**

- 12 V Automotive systems
- Motors, lighting and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

#### Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	100	Α	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	194	W	
Static characte	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	2.47	3	mΩ	
Dynamic characteristics								
$Q_{GD}$	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 32 \text{ V};$ Fig. 13; Fig. 14		-	10.7	-	nC	

<sup>[1]</sup> Continuous current is limited by package.



N-channel 40 V 3.0 m $\Omega$  logic level MOSFET in LFPAK56

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D I
2	S	source	<u> </u>	
3	S	source	q j	G_U: 4
4	G	gate	و و و و	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9Y3R0-40E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9Y3R0-40E	93E040

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$		-	40	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-10	10	V
		T <sub>j</sub> ≤ 175 °C; Pulsed	[1][2]	-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	194	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>	<u>[3]</u>	-	100	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>	[3]	-	100	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 3		-	718	Α

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#### N-channel 40 V 3.0 mΩ logic level MOSFET in LFPAK56

Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drain diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[3]	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	718	Α
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 100 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[4][5]	-	193.8	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering  $\rm T_j$  and or  $\rm V_{GS}$
- [2]
- Continuous current is limited by package. [3]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [4]
- Refer to application note AN10273 for further information.

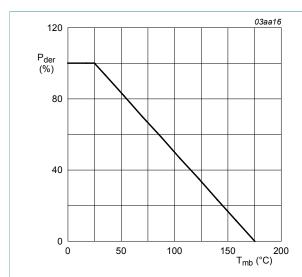
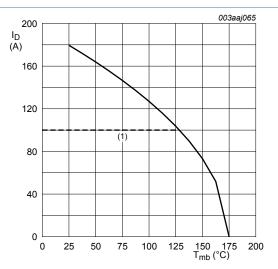


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times \textbf{100 \%}$$



(1) Capped at 100A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 5V$$

#### N-channel 40 V 3.0 mΩ logic level MOSFET in LFPAK56

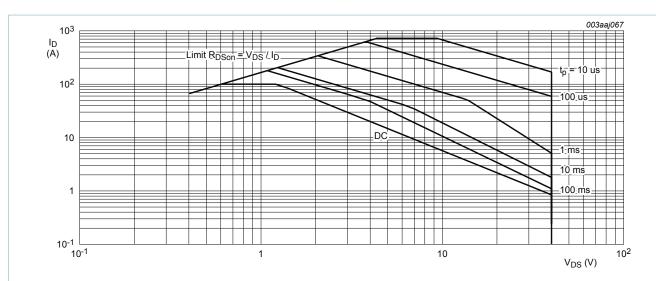
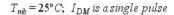


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



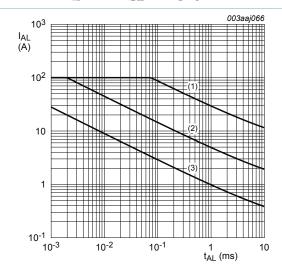


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1)  $T_{j \ (int)} = 25^{\circ}C$ ; (2)  $T_{j \ (int)} = 150^{\circ}C$ ; (3) Repetitive Avalanche

#### 9. Thermal characteristics

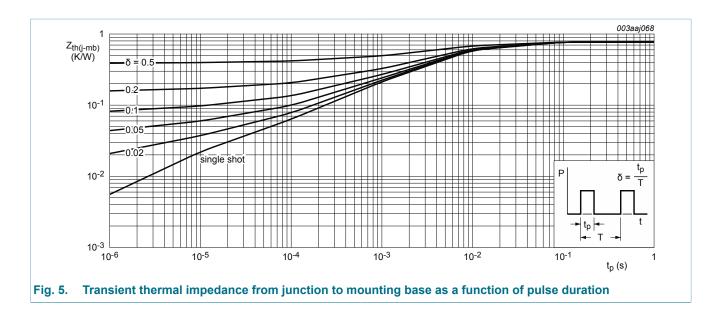
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	0.77	K/W

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### N-channel 40 V 3.0 m $\Omega$ logic level MOSFET in LFPAK56



# 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			'		
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.13	10	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	2.47	3	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	1.98	2.5	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-	6	mΩ
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 5 V;	-	35.5	-	nC
$Q_{GS}$	gate-source charge	Fig. 13; Fig. 14	-	11.7	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$Q_{GD}$	gate-drain charge			-	10.7	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 15$		-	4471	5962	pF
C <sub>oss</sub>	output capacitance			-	563	676	pF
C <sub>rss</sub>	reverse transfer capacitance			-	251	344	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $R_{L}$ = 1.2 $\Omega$ ; $V_{GS}$ = 5 V; $R_{G(ext)}$ = 5 $\Omega$		-	24	-	ns
t <sub>r</sub>	rise time			-	44	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	53	-	ns
t <sub>f</sub>	fall time			-	34	-	ns
Source-dra	ain diode		'				
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 ^{\circ}\text{C}$ ; Fig. 16		-	0.81	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	30	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V		-	25	-	nC

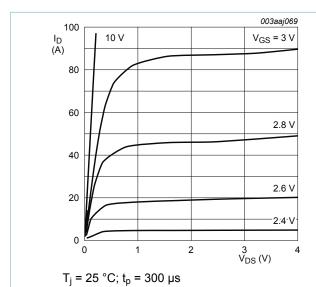


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

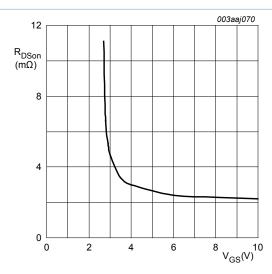


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

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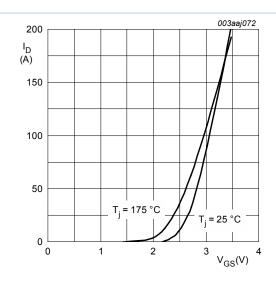


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



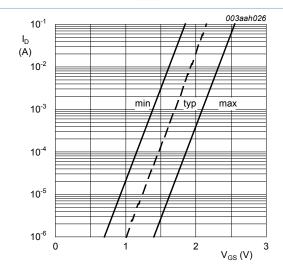


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C;  $V_{DS} = 5V$ 

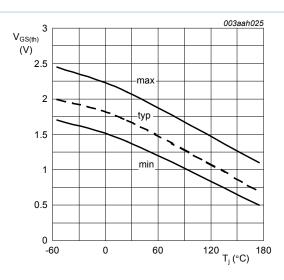
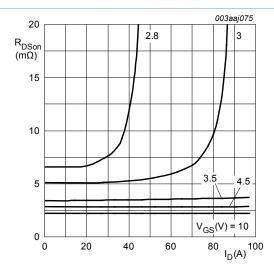


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$



 $T_j = 25 \, ^{\circ}C; t_p = 300 \, \mu s$ 

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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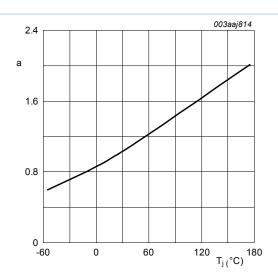


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

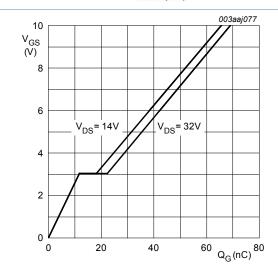


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

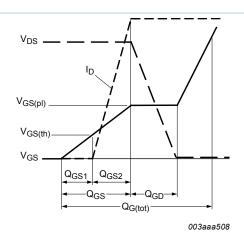


Fig. 13. Gate charge waveform definitions

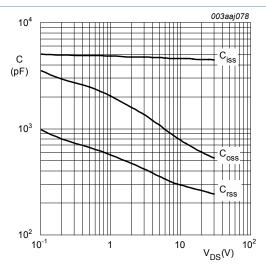


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

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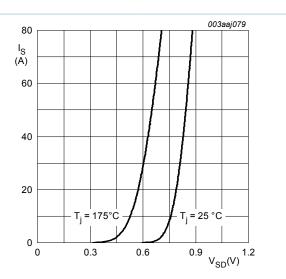
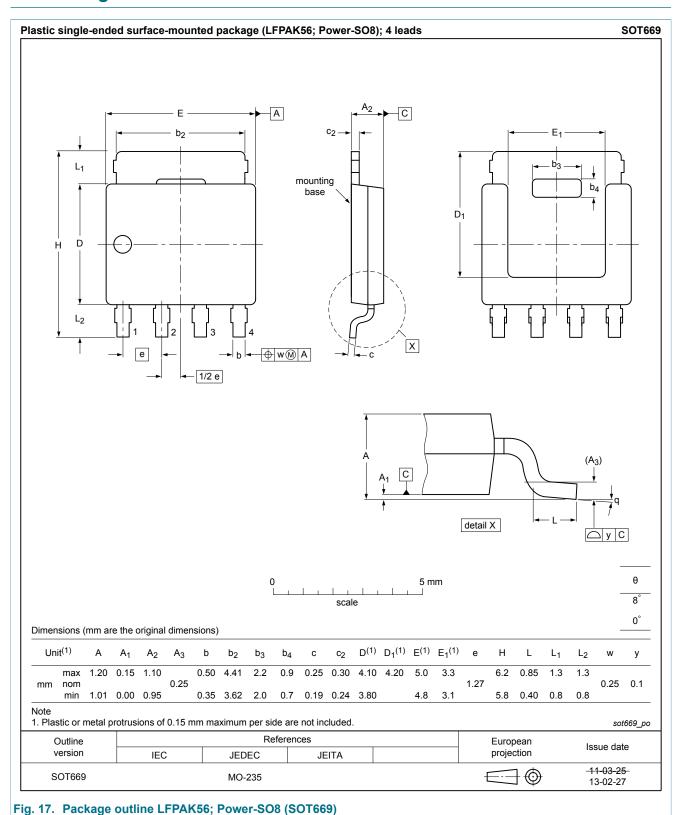


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

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# 11. Package outline



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#### N-channel 40 V 3.0 mΩ logic level MOSFET in LFPAK56

### 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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